

35.C10530C/D2



PATENT APPLICATION

#5  
Pee  
Amatt  
(B)  
10/27/99  
A. Jenkins

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
KIYOFUMI SAKAGUCHI, ET AL. ) Examiner: Not Yet Assigned  
Application No.: 09/161,774 ) Group Art Unit: ~~2812~~ 2823  
Filed: September 29, 1998 )  
For: PROCESS FOR PRODUCTION )  
OF SEMICONDUCTOR )  
SUBSTRATE ) September 22, 1999

Assistant Commissioner for Patents  
Washington, D.C. 20231

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SECOND PRELIMINARY AMENDMENT

Sir:

Prior to examination on the merits, please further amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel Claims 22 - 96 without prejudice to or disclaimer of the subject matter recited therein.

Please add new Claims 97 through 104 as follows:

97. A method for separating a semiconductor layer from a substrate, comprising:

forming a porous layer on a surface of a substrate by an anodic oxidization;